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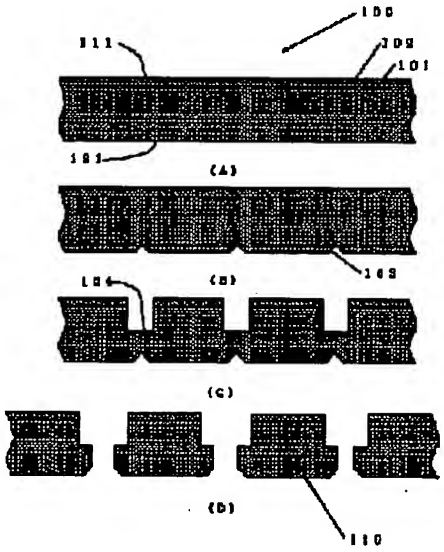
(54) MANUFACTURE OF NITRIDE SEMICONDUCTOR ELEMENT

(57) Abstract

PROBLEM TO BE SOLVED: To especially provide a method for manufacturing a nitride semiconductor element which enables separation of a nitride semiconductor element formed on a substrate with high yield, related to a method for manufacturing a light-emitting diode or a laser diode capable of emitting ultraviolet to orange lights and furthermore a group III-V semiconductor element that can be driven at high temperatures.

SOLUTION: A method for manufacturing a nitride semiconductor element 110, in which a semiconductor wafer 100 having a nitride semiconductor 102 formed on a substrate 101 is divided into nitride semiconductor elements 110, and in particular includes a step of radiating a laser beam through a semiconductor wafer 100 from the side of a first main surface (111) of the semiconductor wafer 100 and/or the side of a second main surface (121) of the semiconductor wafer 100, thus forming a scribe line 103 at a focal point formed at least on the side of the second main surface 121 of the substrate 101 and/or the side of the first main surface (111) of the substrate 101, and a step of separating the semiconductor wafer along the scribe line.



MANUFACTURE OF NITRIDE SEMICONDUCTOR ELEMENT

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Inventor: SHONO HIROBUMI; TOYODA TATSUNORI

Applicant: NICHIA CHEM IND LTD

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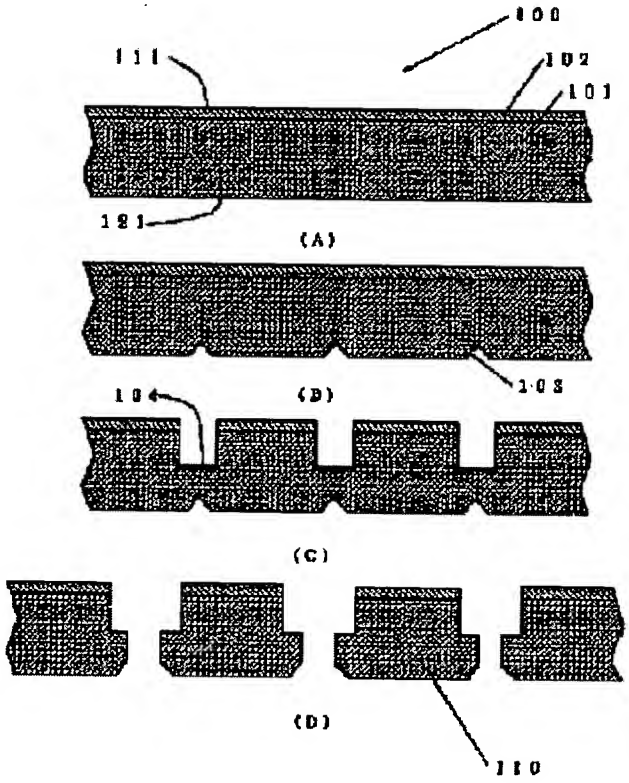

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